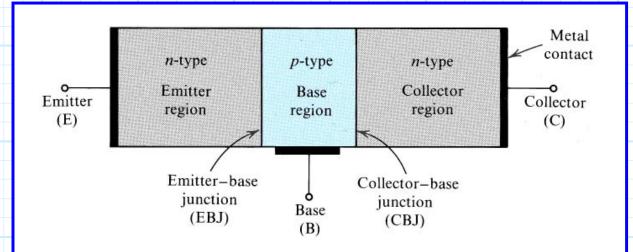
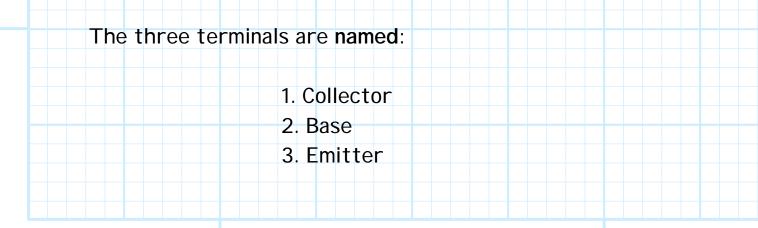
BJT Structure and Modes of Operation

First, let's start with the *npn* Bipolar Junction Transistor (BJT). As the name implies, the *npn* BJT is simply an hunk of p-type Silicon sandwiched between two slices of *n*-type material:



Each of the **three Silicon regions** has one terminal electrode connected to it, and thus the *npn* BJT is a **three terminal** device.



Note that this BJT structure creates two *p*-*n* junctions !

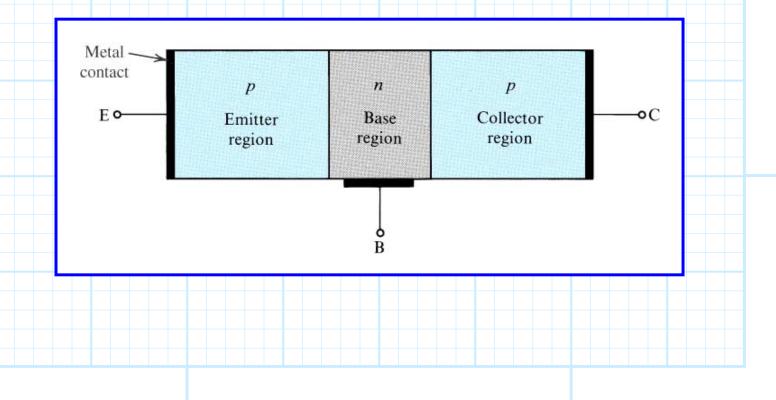
* The junction between the *n*-type collector and the *p*-type base is called the **Collector-Base Junction** (CBJ).

Note for the CBJ, the anode is the _____, and the cathode is the _____.

* The junction between the *n*-type emitter and the *p*-type base is called the **Emitter-Base Junction** (EBJ).

Note for the EBJ, the anode is the _____, and the cathode is the _____.

Now, we find that the *pnp* BJT is simply the **complement** of the *npn* BJT—the *n*-type silicon becomes *p*-type, and vice versa:



Thus, the *pnp* BJT **likewise** has **three** terminals (with the same names as the *npn*), as well as **two** *p*-*n* junctions (the CBJ and the EBJ).

For the *pnp* BJT, the **anode** of the **CBJ** is the _____, and the **cathode** of the **CBJ** is the _____.

Likewise, the anode of the EBJ is the _____, and the cathode of the EBJ is the _____.

Now, we know that each *p*-*n* junction (for either *npn* or *pnp*) has three possible modes:

- 1. forward biased
- 2. reverse biased
- 3. breakdown

We find that **breakdown** is **not** generally a useful mode for transistor operation, and so we will **avoid** that mode.

Given then that there are **two useful** *p*-*n* junction modes, and **two** *p*-*n* junctions for each BJT (i.e., CBJ and EBJ), a BJT can be in one of **four** modes!

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1	Reverse	Reverse
2	Forward	Reverse
3	Reverse	Forward
4	Forward	Forward
Now, let's give each o MODE	of these four BJT mo EBJ	des a name: CBJ
MODE	EBJ	CBJ
MODE	EBJ Reverse	CBJ Reverse

